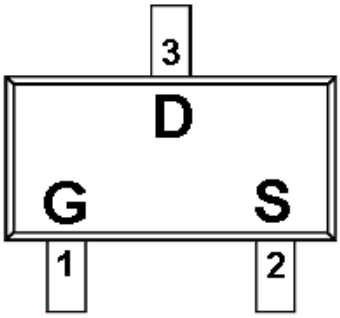
SPN3414W
N-Channel Enhancement Mode MOSFET

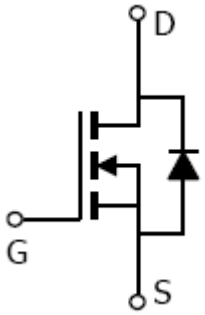
DESCRIPTION
The SPN3414 is the N-Channel logic enhancement mode power field effect transistors are produced using high cell density , DMOS trench technology.
This high density process is especially tailored to minimize on-state resistance.
These devices are particularly suited for low voltage application such as cellular phone and notebook computer power management and other battery powered circuits where high-side switching , and low in-line power loss are needed in a very small outline surface mount package.

FEATURES
- 20V/4.0A,$R_{DS(ON)}$=55mΩ@V_{GS}=4.5V
- 20V/3.4A,$R_{DS(ON)}$=70mΩ@V_{GS}=2.5V
- 20V/2.8A,$R_{DS(ON)}$=90mΩ@V_{GS}=1.8V
- Super high density cell design for extremely low R_{DS} (ON)
- Exceptional on-resistance and maximum DC current capability
- SOT-23 package design

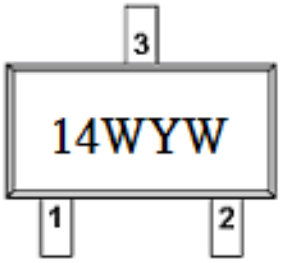
APPLICATIONS
- Power Management in Note book
- Portable Equipment
- Battery Powered System
- DC/DC Converter
- Load Switch
- DSC
- LCD Display inverter

PIN CONFIGURATION(SOT-23)





PART MARKING



Y : Year Code
W : Week Code

SPN3414W
N-Channel Enhancement Mode MOSFET

PIN DESCRIPTION

Pin	Symbol	Description
1	G	Gate
2	S	Source
3	D	Drain

ORDERING INFORMATION

Part Number	Package	Part Marking
SPN3414WS23RGB	SOT-23	14W

※ Week Code : A ~ Z(1 ~ 26) ; a ~ z(27 ~ 52)
※ SPN3414WS23RGB : Tape Reel ; Pb – Free ; Halogen – Free

ABSOULTE MAXIMUM RATINGS

(T_A=25℃ Unless otherwise noted)

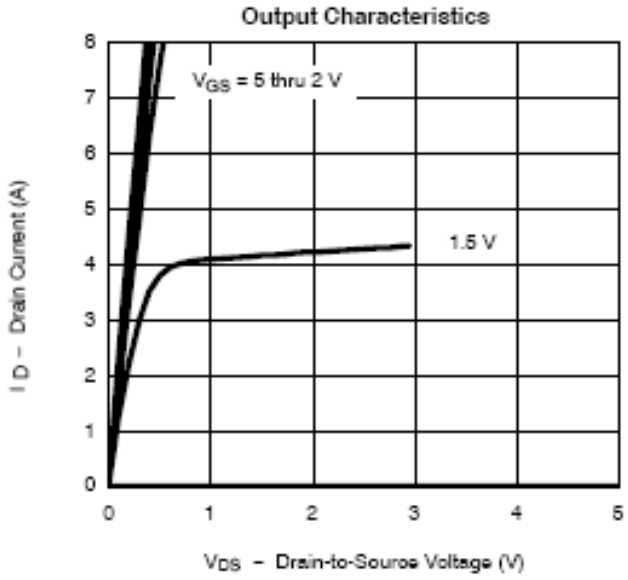
Parameter		Symbol	Typical	Unit
Drain-Source Voltage		V_{DSS}	20	V
Gate –Source Voltage		V_{GSS}	±12	V
Continuous Drain Current(T_J=150℃)	T_A=25℃	I_D	4.0	A
	T_A=70℃		3.4	
Pulsed Drain Current		I_{DM}	10	A
Continuous Source Current(Diode Conduction)		I_S	1.6	A
Power Dissipation	T_A=25℃	P_D	1.25	W
	T_A=70℃		0.8	
Operating Junction Temperature		T_J	-55/150	℃
Storage Temperature Range		T_{STG}	-55/150	℃
Thermal Resistance-Junction to Ambient		$R_{\theta JA}$	105	℃/W

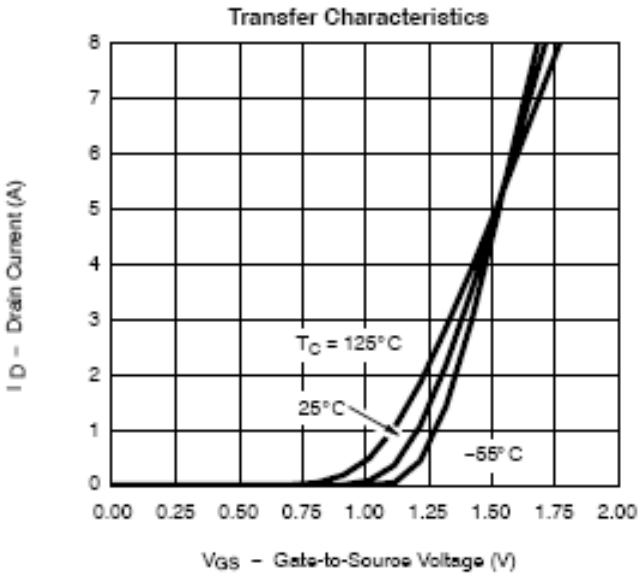
ELECTRICAL CHARACTERISTICS

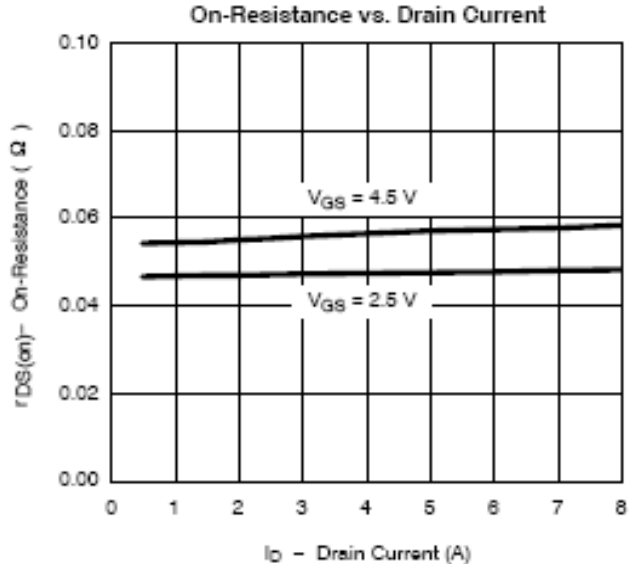
(T_A=25℃ Unless otherwise noted)

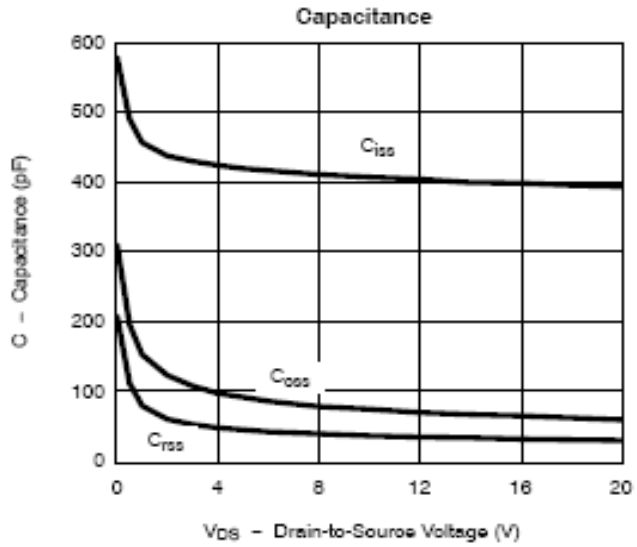
Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS}=0V,I_D=250uA	20			V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=250uA	0.4		1.0	
Gate Leakage Current	I_{GSS}	V_{DS}=0V,V_{GS}=±12V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=20V,V_{GS}=0V			1	uA
		V_{DS}=20V,V_{GS}=0V T_J=55℃			5	
On-State Drain Current	$I_{D(on)}$	V_{DS}≦5V,V_{GS}=4.5V	6			A
Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS}=4.5V,I_D=4.0A		0.040	0.055	Ω
		V_{GS}=2.5V,I_D=3.4A		0.055	0.070	
		V_{GS}=1.8V,I_D=2.8A		0.075	0.090	
Forward Transconductance	gfs	V_{DS}=5V,I_D=-3.6A		10		S
Diode Forward Voltage	V_{SD}	I_S=1.6A,V_{GS}=0V		0.8	1.2	V
Dynamic						
Total Gate Charge	Q_g	V_{DS}=6V,V_{GS}=4.5V I_D≡2.8A		4.8	8	nC
Gate-Source Charge	Q_{gs}			1.0		
Gate-Drain Charge	Q_{gd}			1.0		
Input Capacitance	C_{iss}	V_{DS}=6V,V_{GS}=0V f=1MHz		485		pF
Output Capacitance	C_{oss}			85		
Reverse Transfer Capacitance	C_{rss}			40		
Turn-On Time	$t_{d(on)}$	V_{DD}=6V,R_L=6Ω I_D≡1.0A,V_{GEN}=4.5V R_G=6Ω		8	14	nS
	t_r			12	18	
Turn-Off Time	$t_{d(off)}$			30	35	
	t_f			12	16	

TYPICAL CHARACTERISTICS









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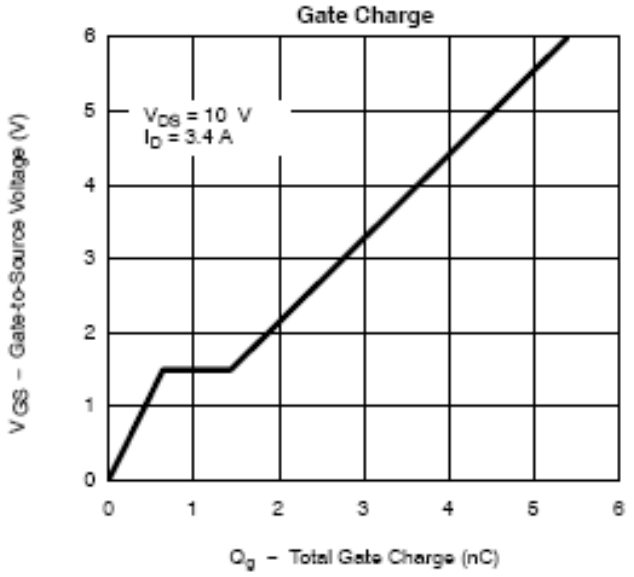

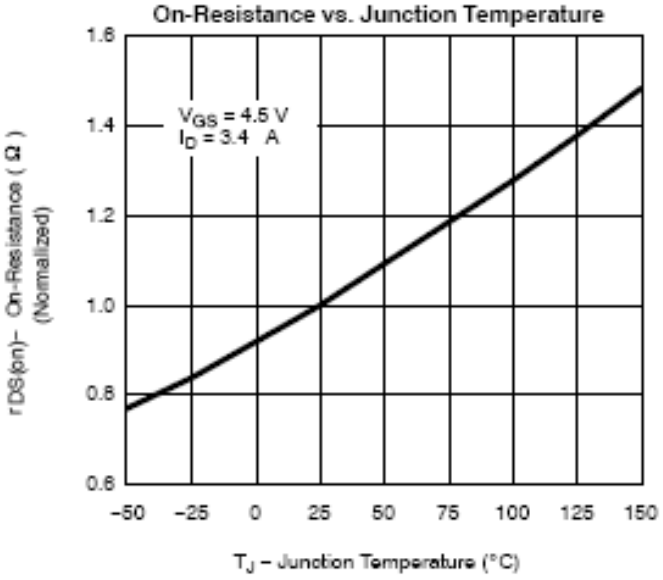

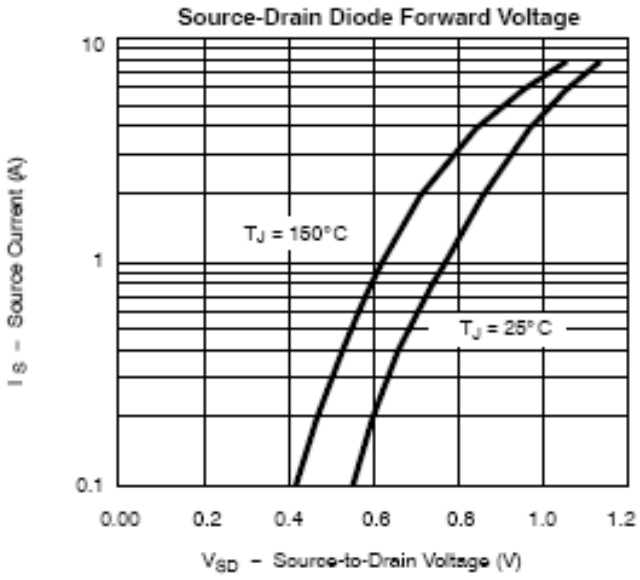

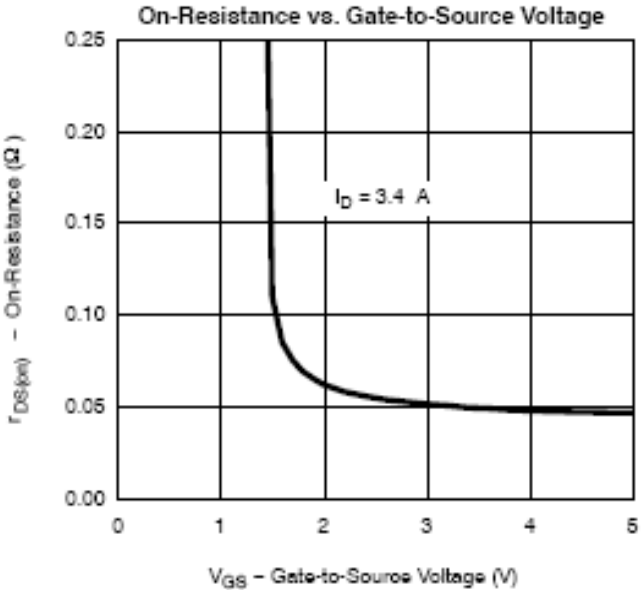

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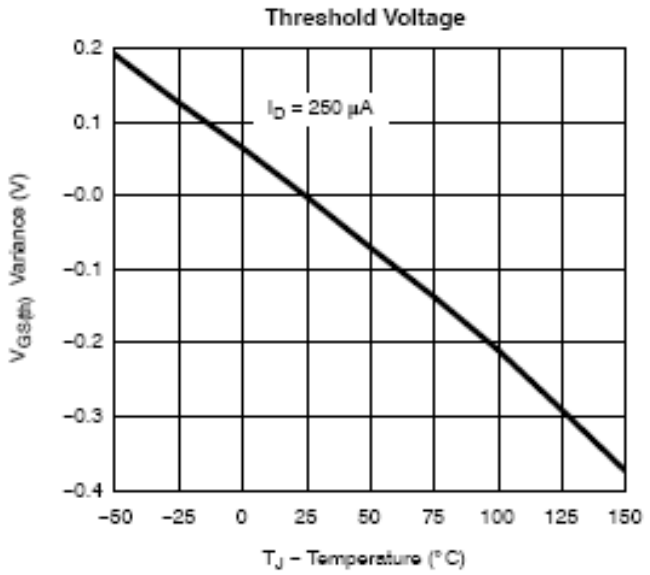

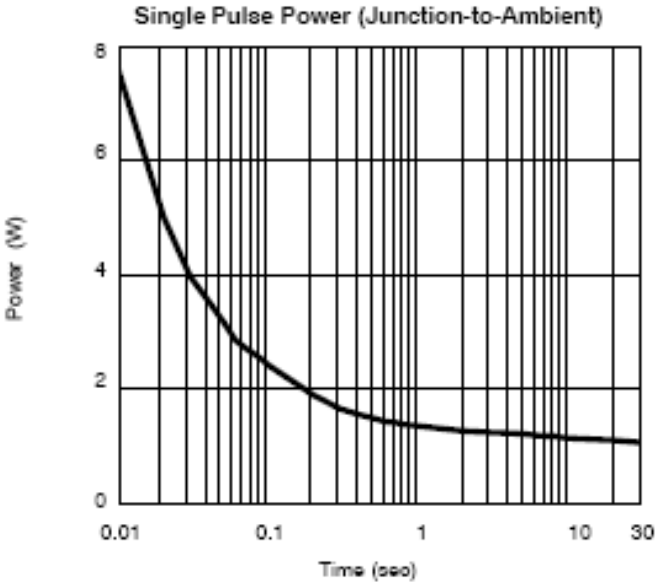

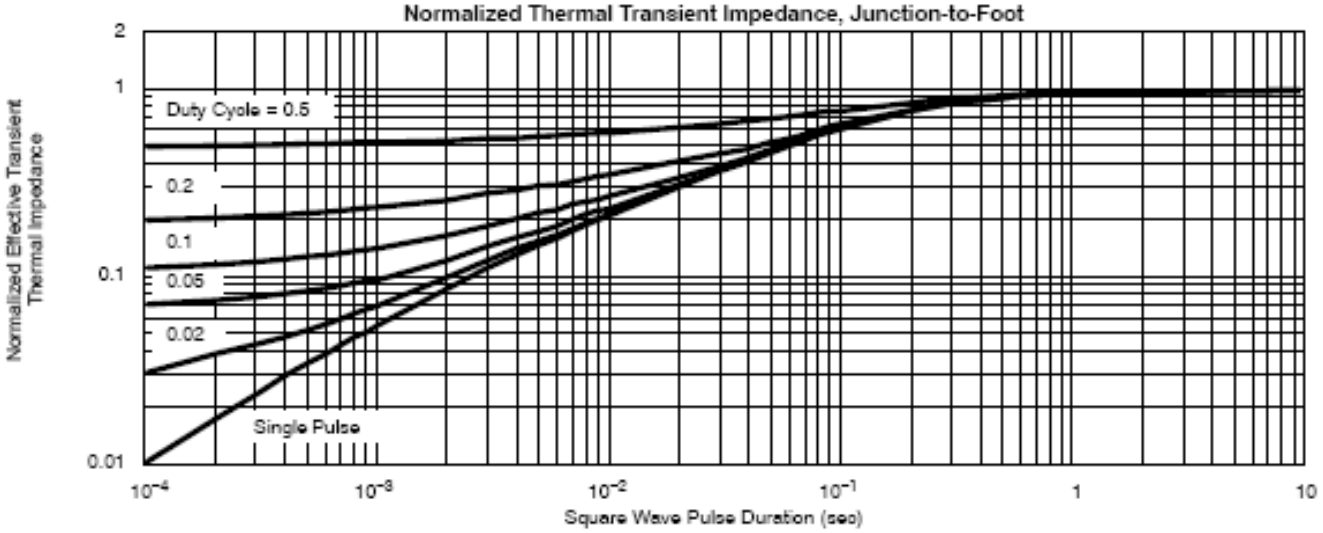

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